

CMSD2005S
SURFACE MOUNT
DUAL, IN SERIES
HIGH VOLTAGE
SILICON SWITCHING DIODES



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD2005S contains two (2) High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SOT-323 surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: B5D

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
 Peak Repetitive Reverse Voltage
 Peak Repetitive Reverse Current
 Continuous Forward Current
 Peak Repetitive Forward Current
 Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
 Peak Forward Surge Current, $t_p=1.0\text{s}$
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL

V_R 300
 V_{RRM} 350
 I_{RRM} 200
 I_F 225
 I_{FRM} 625
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 275
 T_J, T_{stg} -65 to +150
 Θ_{JA} 455

UNITS

V
 V
 mA
 mA
 mA
 A
 A
 mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

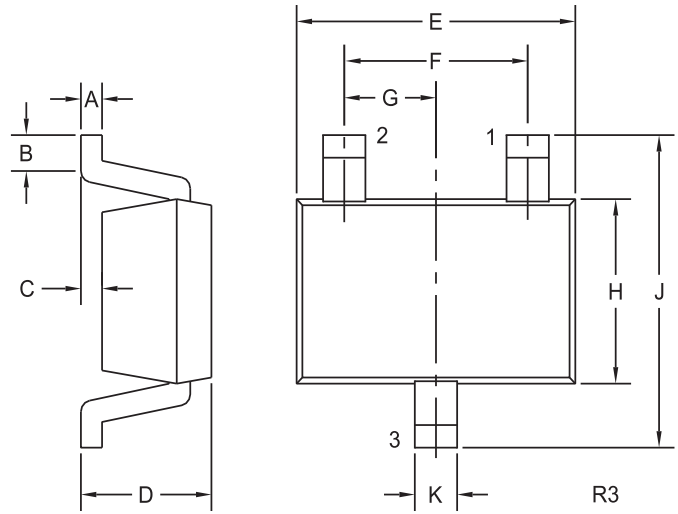
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=280\text{V}$		100	nA
I_R	$V_R=280\text{V}, T_A=150^\circ\text{C}$		100	μA
BV_R	$I_R=100\mu\text{A}$	350		V
V_F	$I_F=20\text{mA}$		0.87	V
V_F	$I_F=100\text{mA}$		1.0	V
V_F	$I_F=200\text{mA}$		1.25	V
C_T	$V_R=0, f=1.0\text{MHz}$		5.0	pF
t_{rr}	$I_R=I_F=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		50	ns

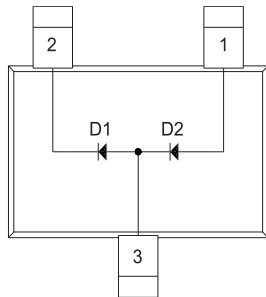
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SOT-323 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D2
- 2) Cathode D1
- 3) Anode D1, Cathode D2

MARKING CODE: B5D

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.002	0.008	0.05	0.20
B	0.004	-	0.10	-
C	-	0.004	-	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.045	0.053	1.15	1.35
J	0.079	0.087	2.00	2.20
K	0.008	0.016	0.20	0.40

SOT-323 (REV: R3)

R1 (8-February 2010)